

567-851

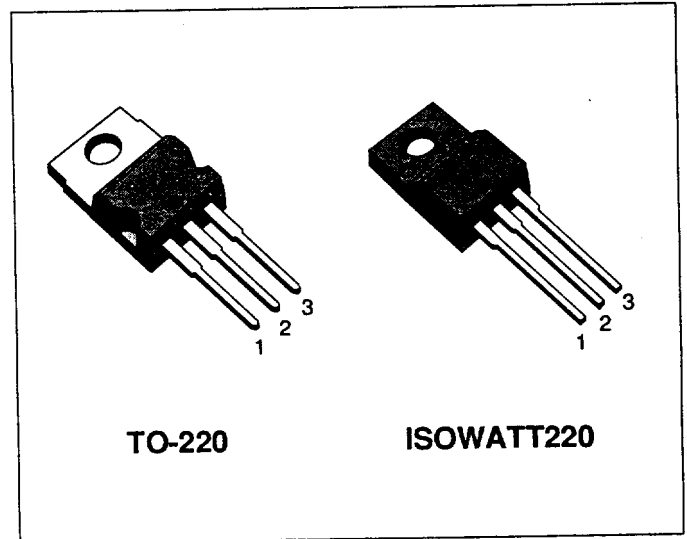
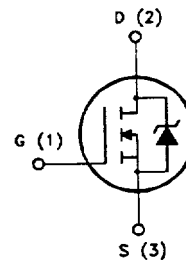
**N - CHANNEL ENHANCEMENT MODE  
 POWER MOS TRANSISTOR**

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP5N90	900 V	< 2.4 Ω	5 A
STP5N90FI	900 V	< 2.4 Ω	2.8 A

- TYPICAL R<sub>DS(on)</sub> = 1.9 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION

**APPLICATIONS**

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)


**INTERNAL SCHEMATIC DIAGRAM**

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value		Unit
		STP5N90	STP5N90FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	900		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	900		V
V <sub>GS</sub>	Gate-source Voltage	± 20		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	5	2.8	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	3	1.7	A
I <sub>DM</sub> (*)	Drain Current (pulsed)	20	20	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	125	40	W
	Derating Factor	1	0.32	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	2000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(\*) Pulse width limited by safe operating area

## THERMAL DATA

			TC-22C	ISOWATT220	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	-	3.12	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max		62.5	°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ		0.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose			300	°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	5	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	270	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	13	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	3	A

ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	900			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C			250 1000	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 2.5 A V <sub>GS</sub> = 10V I <sub>D</sub> = 2.5 A T <sub>c</sub> = 100°C		1.9	2.4 4.8	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	5			A

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 2.5 A	2	4		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1190	1450	pF
C <sub>oss</sub>	Output Capacitance			165	200	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70	85	pF



**ELECTRICAL CHARACTERISTICS (continued)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D = 2.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		50	65	ns
$t_r$	Rise Time			85	105	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 640\text{ V}$ $I_D = 5.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		200		A/ $\mu$ s
$Q_g$	Total Gate Charge	$V_{DD} = 500\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 10\text{ V}$		75	95	nC
$Q_{gs}$	Gate-Source Charge			9		nC
$Q_{gd}$	Gate-Drain Charge			33		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 5.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		120	150	ns
$t_f$	Fall Time			30	40	ns
$t_c$	Cross-over Time			160	200	ns

**SOURCE DRAIN DIODE**

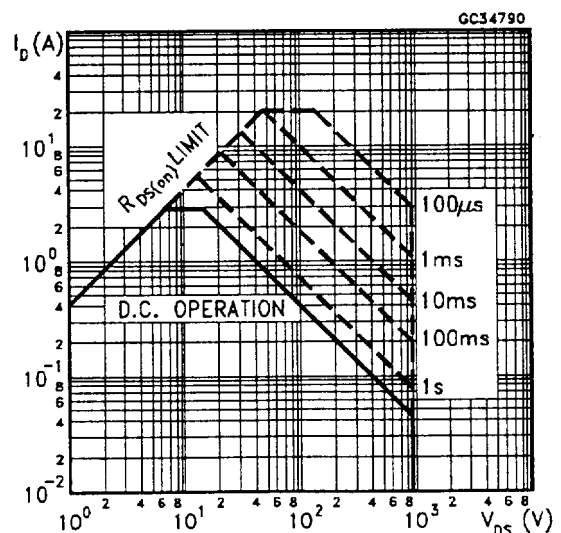
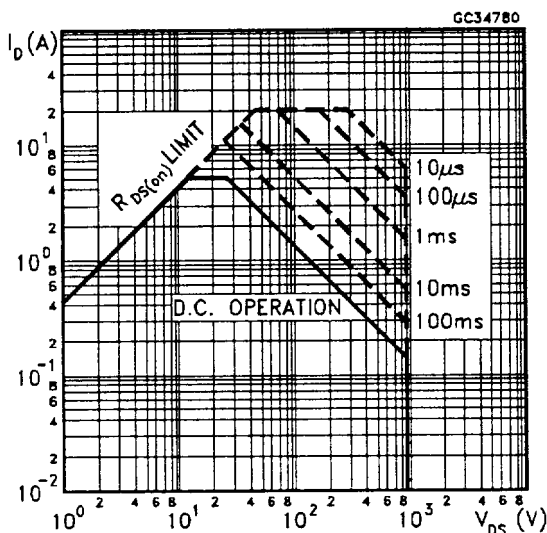
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				20	A
$V_{SD}$	Forward On Voltage	$I_{SD} = 5\text{ A}$ $V_{GS} = 0$			2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 80\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		700		ns
$Q_{rr}$	Reverse Recovery Charge				7.7	$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current				22	A

(\*) Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

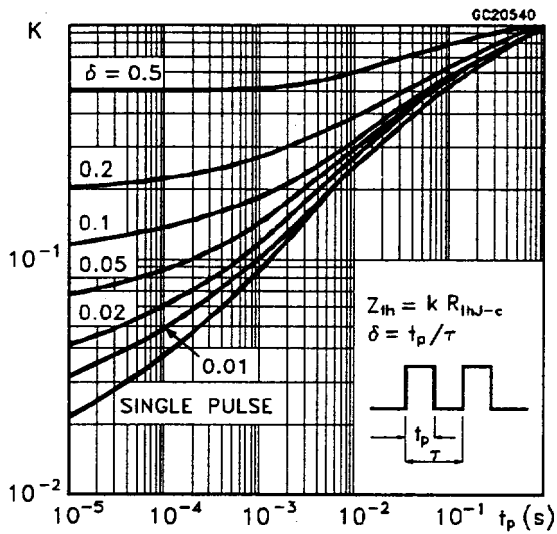
( $\bullet$ ) Pulse width limited by safe operating area

**Safe Operating Areas For TO-220**

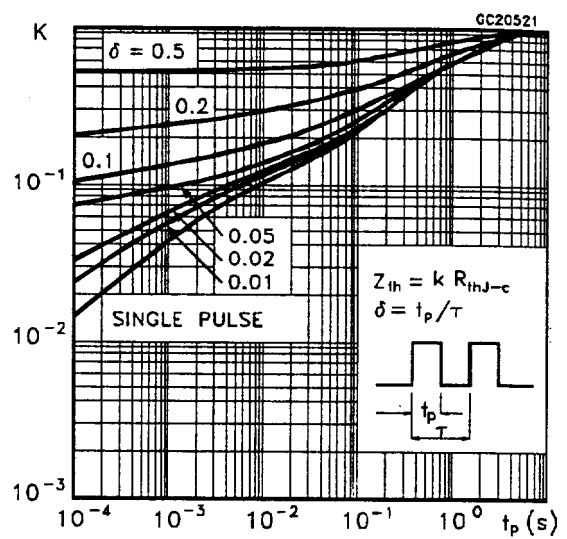
**Safe Operating Areas For ISOWATT220**



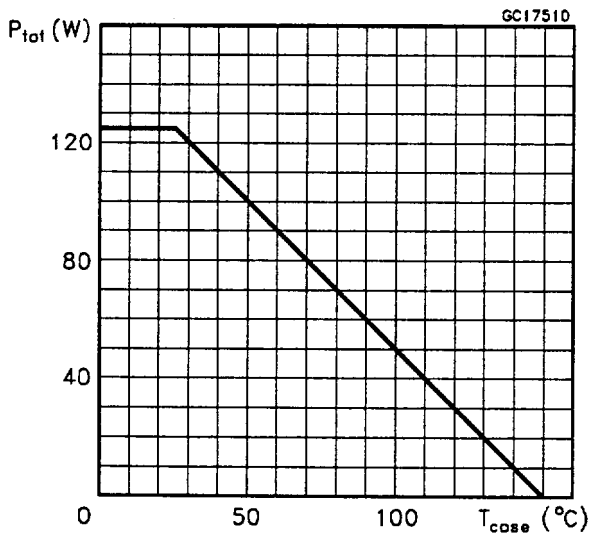
Thermal Impedance For TO-220



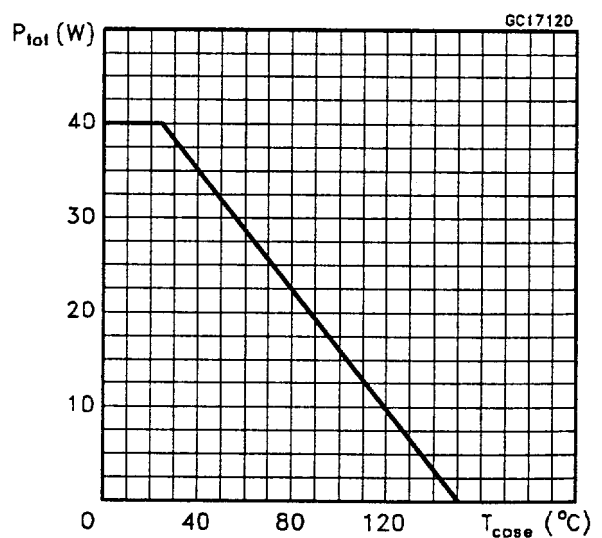
Thermal Impedance For ISOWATT220



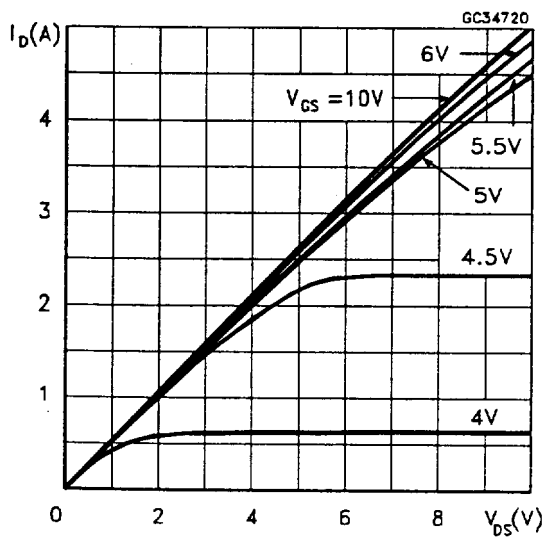
Derating Curve For TO-220



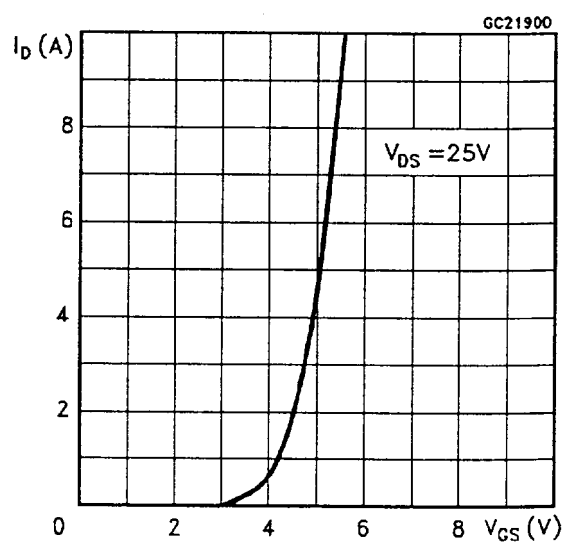
Derating Curve For ISOWATT220



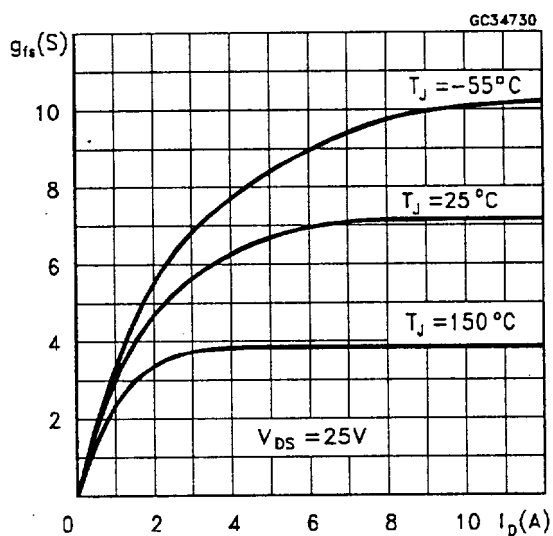
Output Characteristics



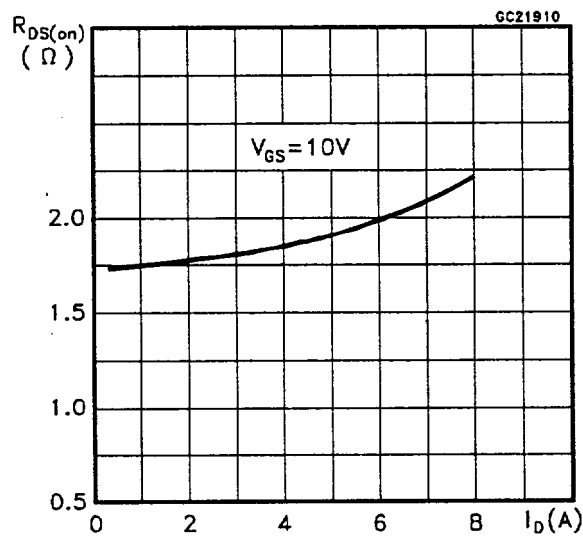
Transfer Characteristics



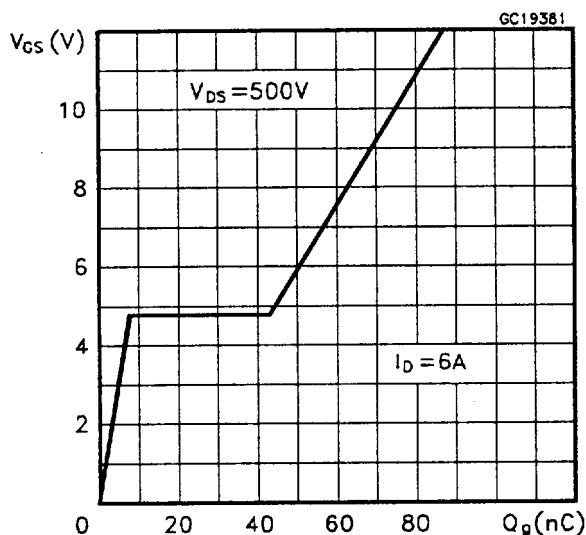
Transconductance



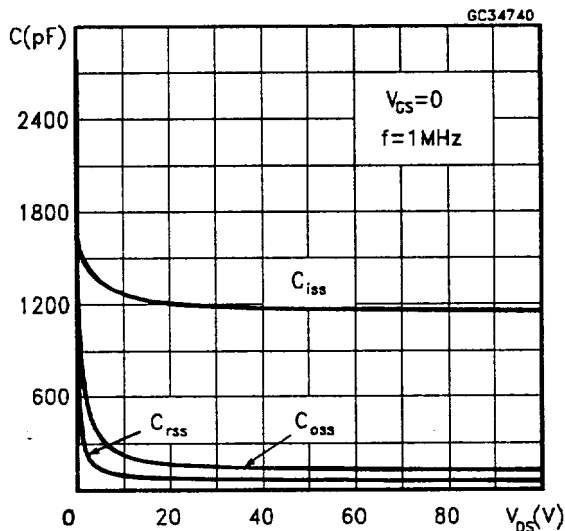
Static Drain-source On Resistance



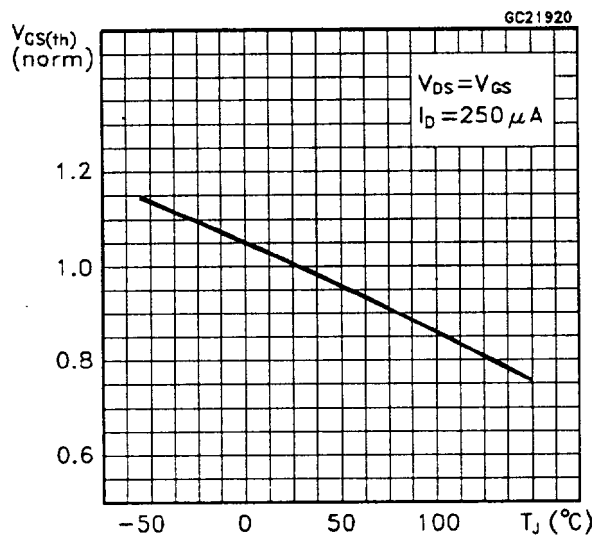
Gate Charge vs Gate-source Voltage



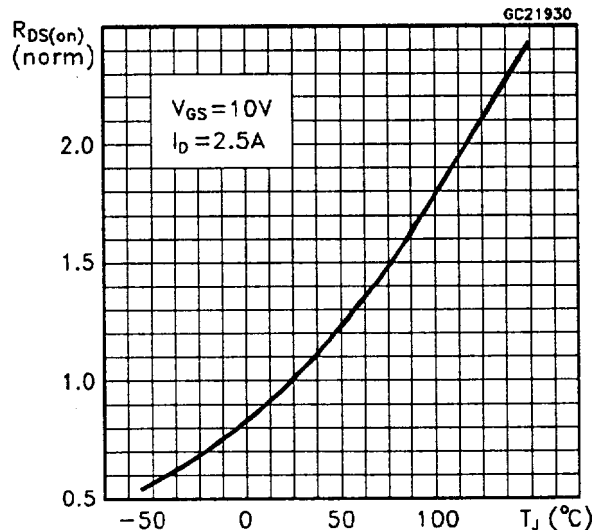
Capacitance Variations



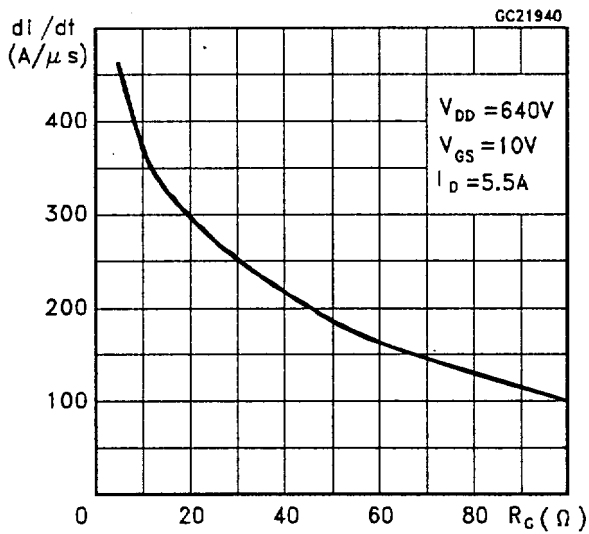
Normalized Gate Threshold Voltage vs Temperature



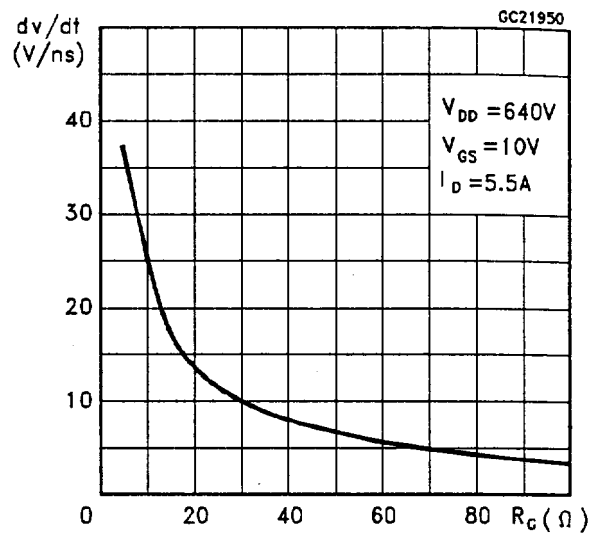
Normalized On Resistance vs Temperature



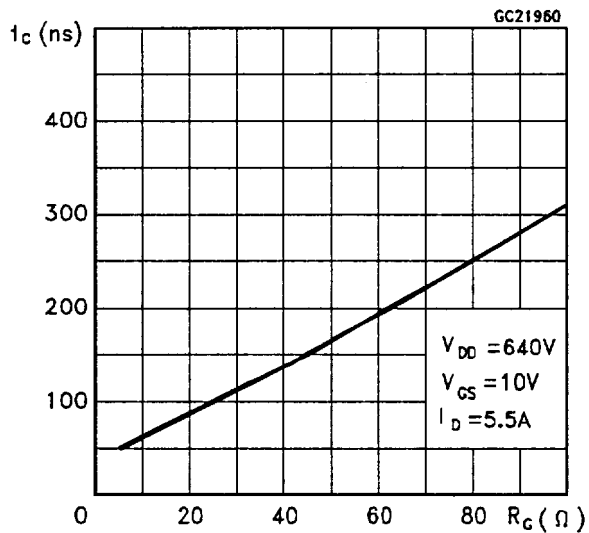
Turn-on Current Slope



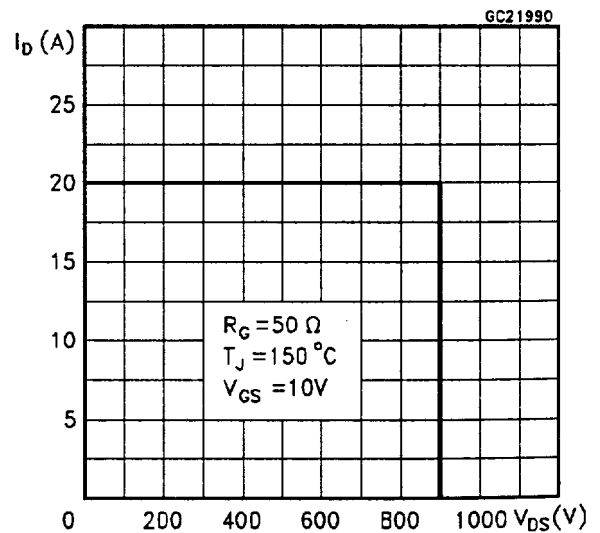
Turn-off Drain-source Voltage Slope



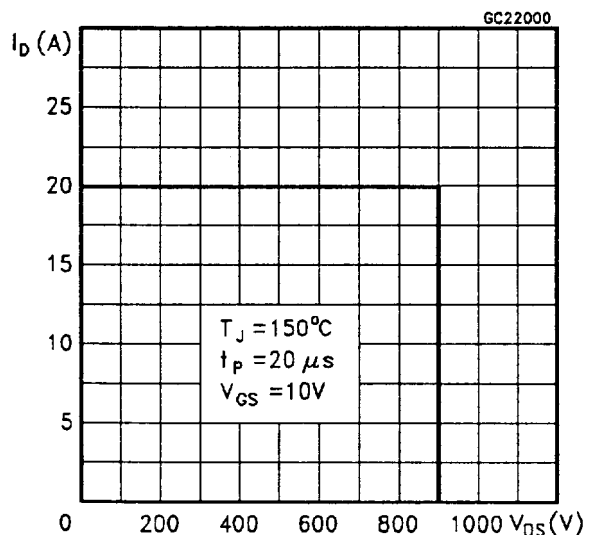
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

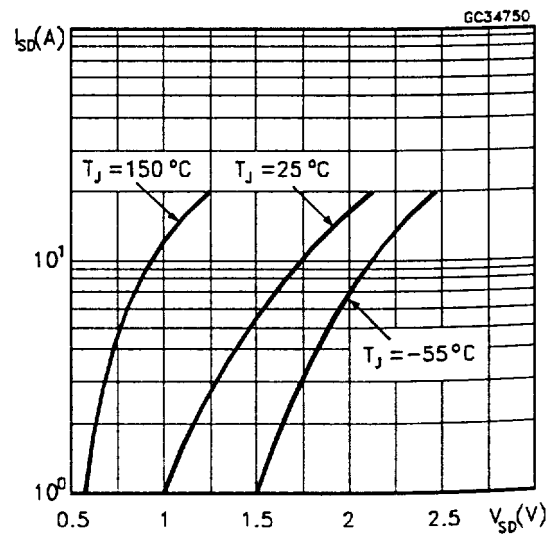






Fig. 1: Unclamped Inductive Load Test Circuits

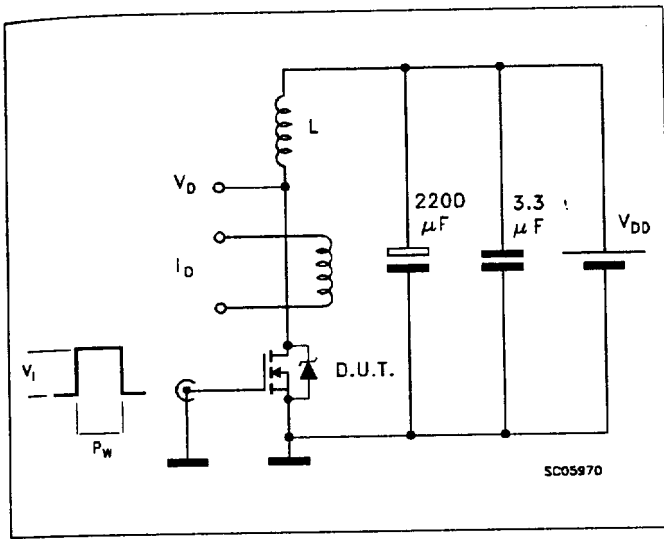


Fig. 2: Unclamped Inductive Waveforms

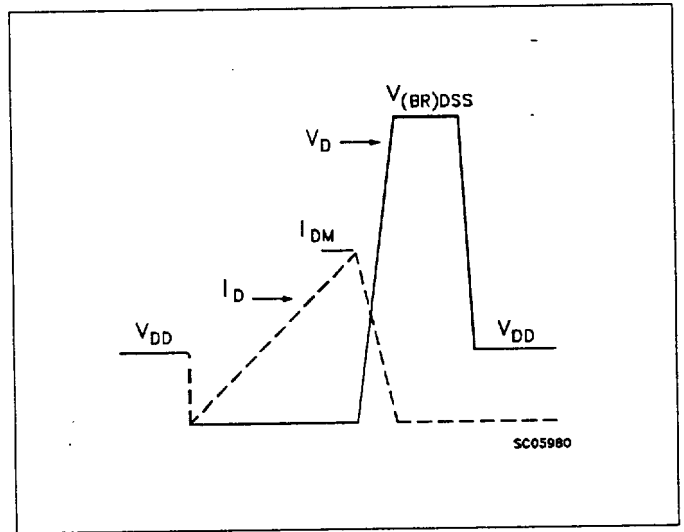


Fig. 3: Switching Times Test Circuits For Resistive Load

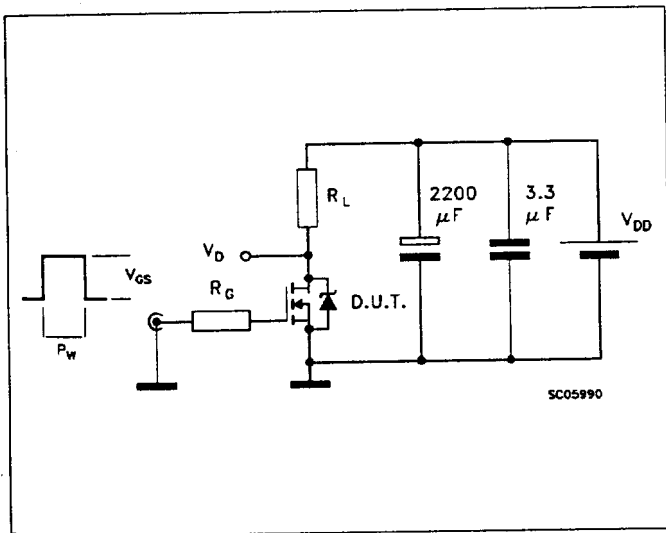


Fig. 4: Gate Charge Test Circuit

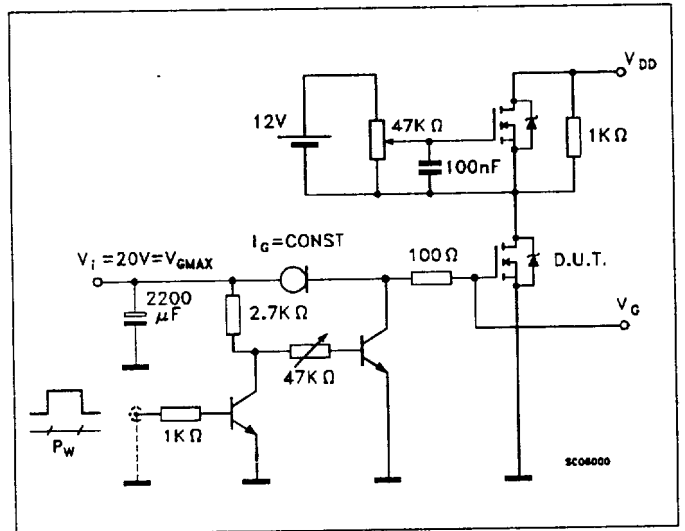
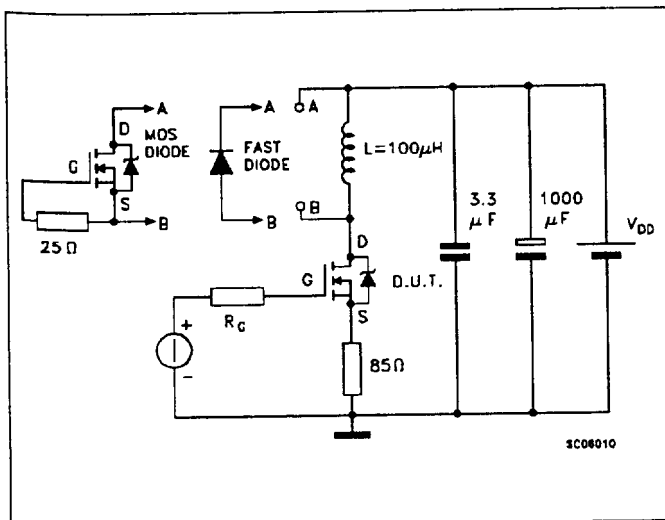


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time



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